

## 1. General description

Ultrafast dual epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

### 2. Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- · Soft recovery characteristic minimizes power consuming oscillations

### 3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

### 4. Quick reference data

	uick reference data	<b>0</b> 11/1					
Symbol	Parameter	Conditions		Values			Unit
Absolute	e maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			100			V
I <sub>O(AV)</sub>	average output current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 115 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u>		20			A
I <sub>RRM</sub>	repetitive peak reverse current	$δ = 0.001; t_p = 2 μs;$		0.2			A
$V_{\text{ESD}}$	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k $\Omega$ ; all pins	8		kV		
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; per diode	20		A		
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125			A	
		$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137			A	
Symbol	Parameter	Conditions	Min Typ Max		Unit		
Static ch	aracteristics	· · · · · · · · · · · · · · · · · · ·					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>		-	0.72	0.85	V
Dynamic	characteristics	1				1	
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5$		-	20	25	ns
		$I_F = 0.5 \text{ A to } I_R = 1 \text{ A}; T_j = 25 \text{ °C};$ measured at $I_R = 0.25 \text{ A};$ step recovery; Fig. 6		-	10	20	ns

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## 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	К	cathode	701	
3	A2	anode 2		
nb	К	mounting base; cathode		K sym125

## 6. Ordering information

Table 3. Ordering information						
Type number         Package						
	Name	Description	Version			
BYV32E-100	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

# 7. Marking

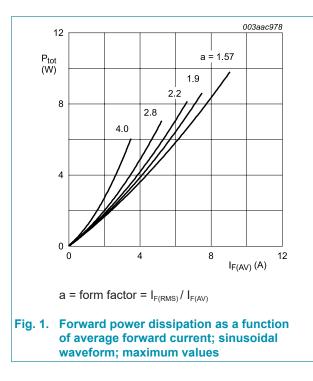
Table 4. Marking codes					
Type number	Marking codes				
BYV32E-100	BYV32E-100				

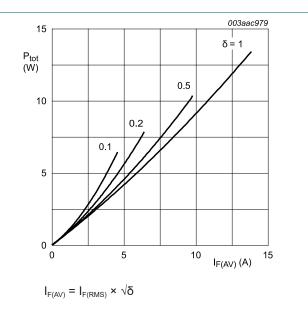
## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		100	V
$V_{\text{RWM}}$	crest working reverse voltage		100	V
V <sub>R</sub>	reverse voltage	DC	100	V
I <sub>O(AV)</sub>	average output current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 115 °C; both diodes conducting; <u>Fig 1</u> ; <u>Fig 2</u>	20	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; per diode	20	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125	A
		$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137	A
I <sub>RRM</sub>	repetitive peak reverse current	$\delta$ = 0.001; t <sub>p</sub> = 2 µs; per diode	0.2	A
I <sub>RSM</sub>	non-repetitive peak reverse current	$t_p$ = 100 µs; per diode	0.2	A
T <sub>stg</sub>	storage temperature		-40 to 150	°C
Tj	junction temperature		150	°C
$V_{\text{ESD}}$	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k $\Omega$	8	kV



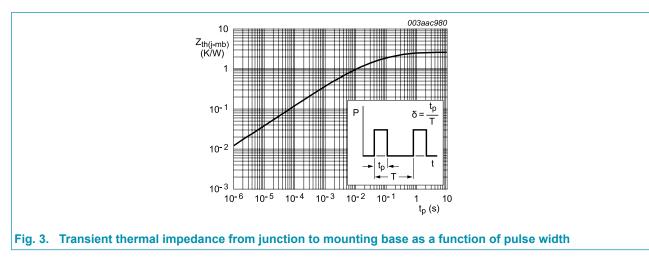




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## 9. Thermal characteristics

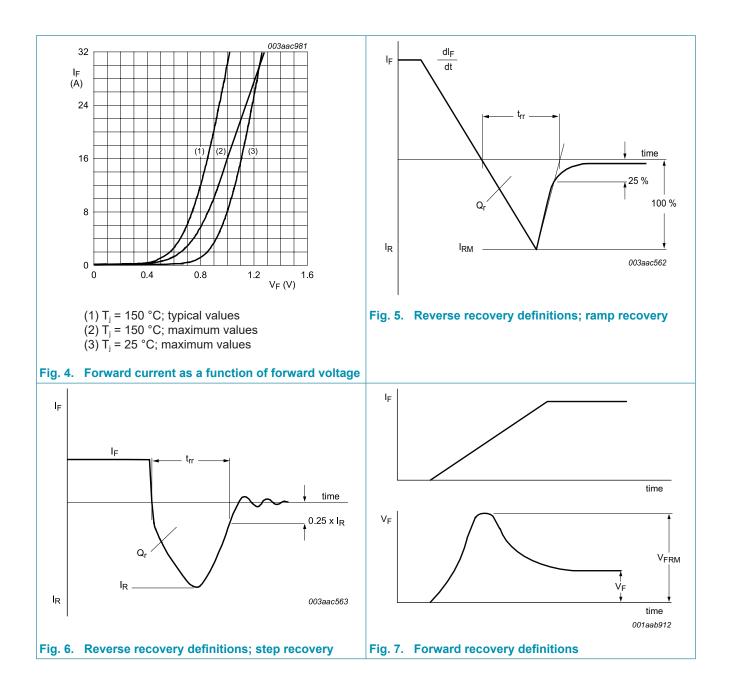
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	with heatsink compound; both diodes conducting	-	-	1.6	K/W
		with heatsink compound; per diode; <u>Fig 3</u>	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W



## **10. Characteristics**

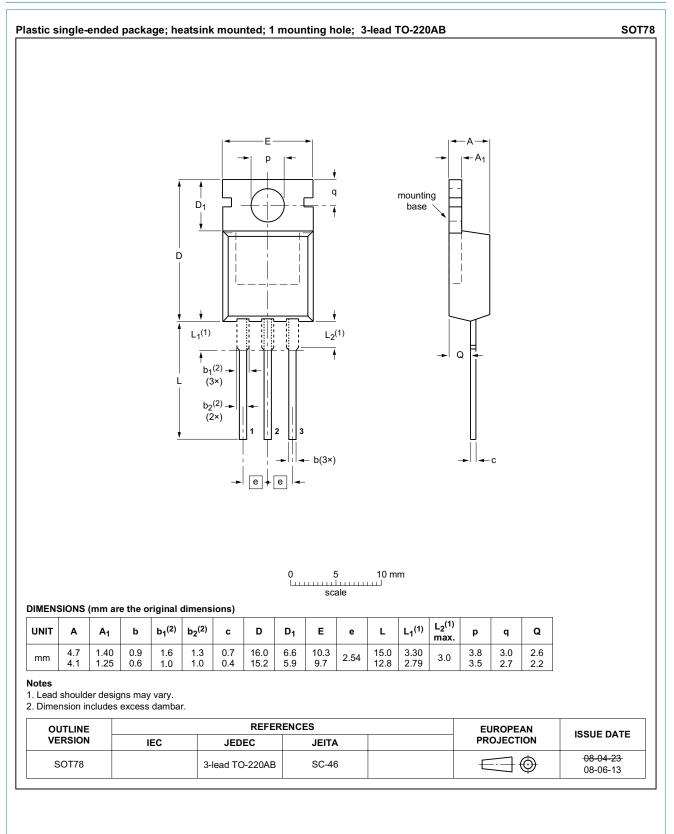
Table 7. Cl	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.72	0.85	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C	-	1	1.15	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C	-	6	30	μA
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}$	-	8	12.5	nC
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; ramp recovery; <u>Fig. 5</u>	-	20	25	ns
		$I_F = 0.5 \text{ A to } I_R = 1 \text{ A}; T_j = 25 \text{ °C};$ measured at $I_R = 0.25 \text{ A};$ step recovery; Fig. 6	-	10	20	ns
V <sub>FR</sub>	forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 10 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	-	1	V

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### **11. Package outline**



## **12. Revision history**

Table 8. Revision histor	/							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
BYV32E-100 v.5	20180307	Product specification	-	BYV32E-100_4				
Modifications:	Change from NXP ve	rsion to WeEn version						
BYV32E-100_4	20090302	Product specification	-	BYV32E_SERIES_3				
<ul> <li>Modifications:</li> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Package outline updated.</li> <li>Type number BYV32E-100 separated from data sheet BYV32E SERIES 3</li> </ul>								
BYV32E_SERIES_3	20010301	Product specification	-	BYV32E_SERIES_2				
BYV32E_SERIES_2	19980701	Product specification	-	BYV32EB_SERIES_1				
BYV32EB_SERIES_1	19960801	Product specification	-	-				

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## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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